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# FDMS86180

## N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET

100 V, 151 A, 3.2 mΩ

### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)} = 3.2\text{ m}\Omega$  at  $V_{GS} = 10\text{ V}$ ,  $I_D = 67\text{ A}$
- Max  $r_{DS(on)} = 7.9\text{ m}\Omega$  at  $V_{GS} = 6\text{ V}$ ,  $I_D = 33\text{ A}$
- 50% Lower Qrr than Other MOSFET Suppliers
- Lowers Switching Noise/EMI
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant

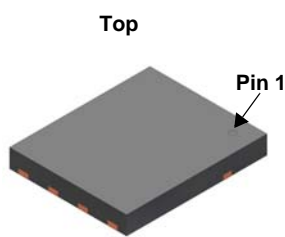


### General Description

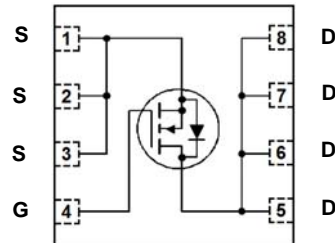
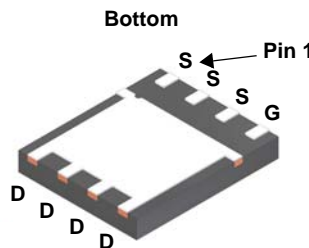
This N-Channel MV MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

### Applications

- Primary DC-DC MOSFET
- Synchronous Rectifier in DC-DC and AC-DC
- Motor Drive
- Solar



Power 56



### MOSFET Maximum Ratings $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	$T_C = 25\text{ }^\circ\text{C}$ (Note 5)	151
	-Continuous	$T_C = 100\text{ }^\circ\text{C}$ (Note 5)	95
	-Continuous	$T_A = 25\text{ }^\circ\text{C}$ (Note 1a)	21
	-Pulsed	(Note 4)	775
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	486
$P_D$	Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	138
	Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$ (Note 1a)	2.7
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	45	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86180	FDMS86180	Power 56	13 "	12 mm	3000 units

FDMS86180 N-Channel Shielded Gate PowerTrench<sup>®</sup> MOSFET

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}, V_{GS} = 0\ \text{V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		73		mV/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}, V_{DS} = 0\ \text{V}$			100	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 370\ \mu\text{A}$	2.0	3.2	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 370\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		-8		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}, I_D = 67\ \text{A}$		2.4	3.2	m $\Omega$
		$V_{GS} = 6\ \text{V}, I_D = 33\ \text{A}$		3.8	7.9	
		$V_{GS} = 10\ \text{V}, I_D = 67\ \text{A}, T_J = 125^\circ\text{C}$		4.0	5.4	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\ \text{V}, I_D = 67\ \text{A}$		144		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 50\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$		4439	6215	pF
$C_{oss}$	Output Capacitance			2663	3730	pF
$C_{rss}$	Reverse Transfer Capacitance			24	55	pF
$R_g$	Gate Resistance		0.1	0.8	1.6	$\Omega$

### Switching Characteristics

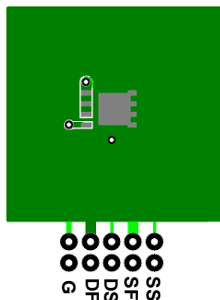
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\ \text{V}, I_D = 67\ \text{A}, V_{GS} = 10\ \text{V}, R_{GEN} = 6\ \Omega$		24	39	ns	
$t_r$	Rise Time			12	22	ns	
$t_{d(off)}$	Turn-Off Delay Time			30	48	ns	
$t_f$	Fall Time			7	14	ns	
$Q_g$	Total Gate Charge		$V_{GS} = 0\ \text{V to } 10\ \text{V}$		60	84	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\ \text{V to } 6\ \text{V}$	$V_{DD} = 50\ \text{V}, I_D = 67\ \text{A}$		38	54	nC
$Q_{gs}$	Gate to Source Charge				20		nC
$Q_{gd}$	Gate to Drain "Miller" Charge				12		nC
$Q_{oss}$	Output Charge	$V_{DD} = 50\ \text{V}, V_{GS} = 0\ \text{V}$			175		nC

### Drain-Source Diode Characteristics

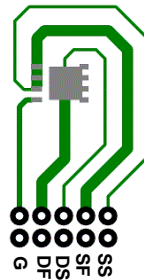
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}, I_S = 2.1\ \text{A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\ \text{V}, I_S = 67\ \text{A}$ (Note 2)		0.8	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 33\ \text{A}, di/dt = 300\ \text{A}/\mu\text{s}$		44	71	ns
$Q_{rr}$	Reverse Recovery Charge			109	207	nC
$t_{rr}$	Reverse Recovery Time	$I_F = 33\ \text{A}, di/dt = 1000\ \text{A}/\mu\text{s}$		33	53	ns
$Q_{rr}$	Reverse Recovery Charge			235	376	nC

#### Notes:

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\ \text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\ \text{in.}$  board of FR-4 material.  $R_{\theta CA}$  is determined by the user's board design.



a)  $45^\circ\text{C}/\text{W}$  when mounted on a  $1\ \text{in}^2$  pad of 2 oz copper



b)  $115^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

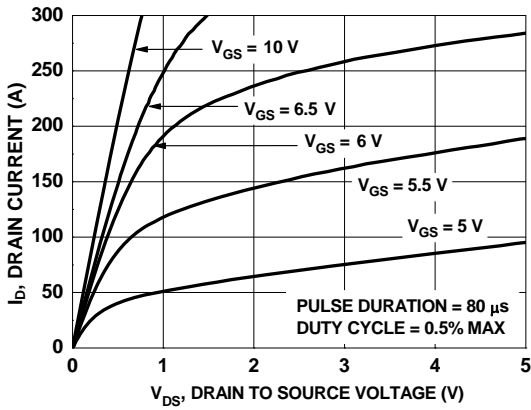
2. Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty cycle < 2.0%.

3.  $E_{AS}$  of 486 mJ is based on starting  $T_J = 25^\circ\text{C}$ , N-ch:  $L = 3\ \text{mH}, I_{AS} = 18\ \text{A}, V_{DD} = 100\ \text{V}, V_{GS} = 10\ \text{V}$ . 100% test at  $L = 0.1\ \text{mH}, I_{AS} = 58\ \text{A}$ .

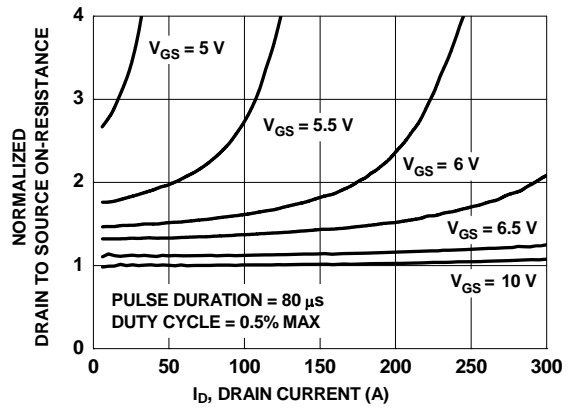
4. Pulsed  $I_d$  please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

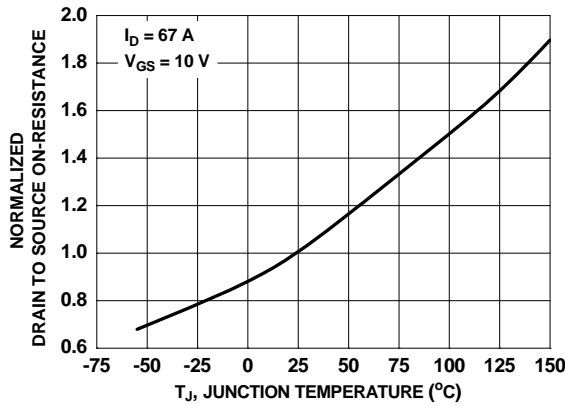
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted.



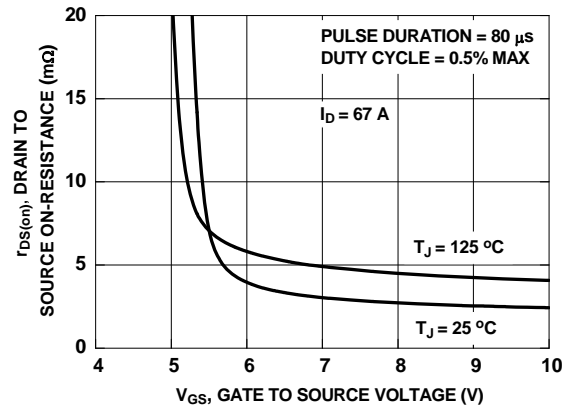
**Figure 1. On-Region Characteristics**



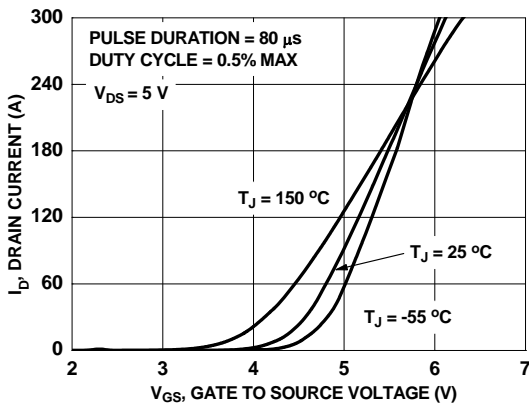
**Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage**



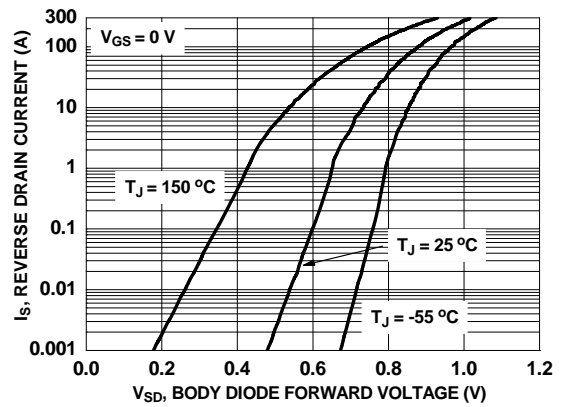
**Figure 3. Normalized On-Resistance vs. Junction Temperature**



**Figure 4. On-Resistance vs. Gate to Source Voltage**

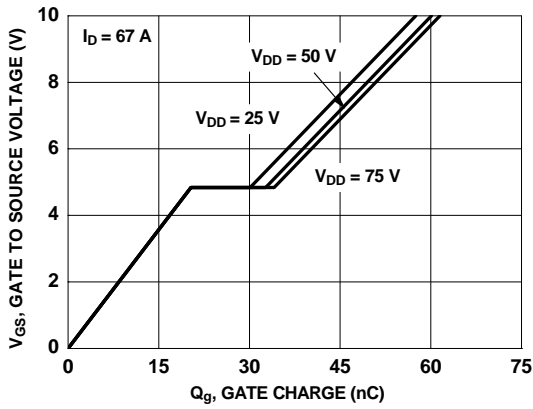


**Figure 5. Transfer Characteristics**

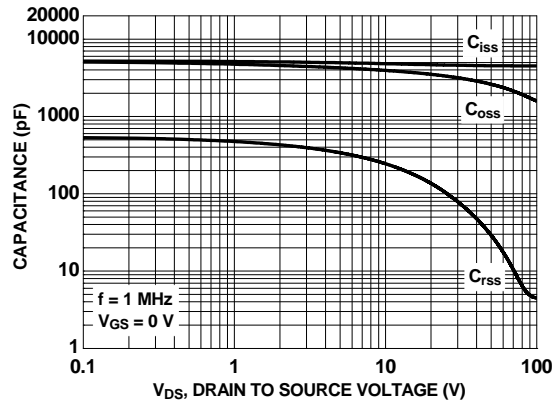


**Figure 6. Source to Drain Diode Forward Voltage vs. Source Current**

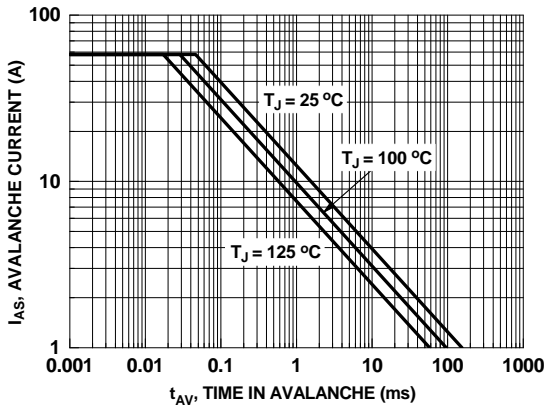
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



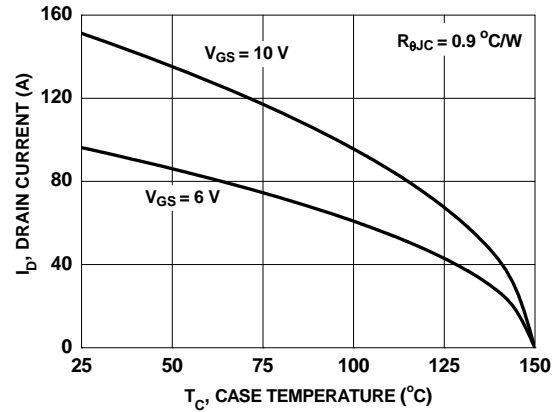
**Figure 7. Gate Charge Characteristics**



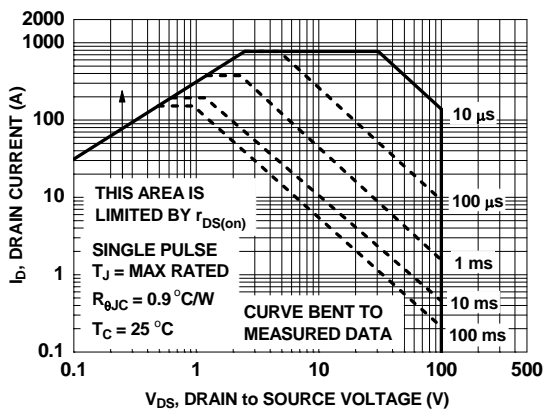
**Figure 8. Capacitance vs. Drain to Source Voltage**



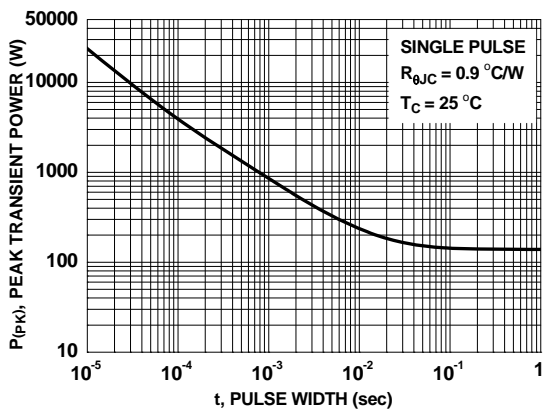
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

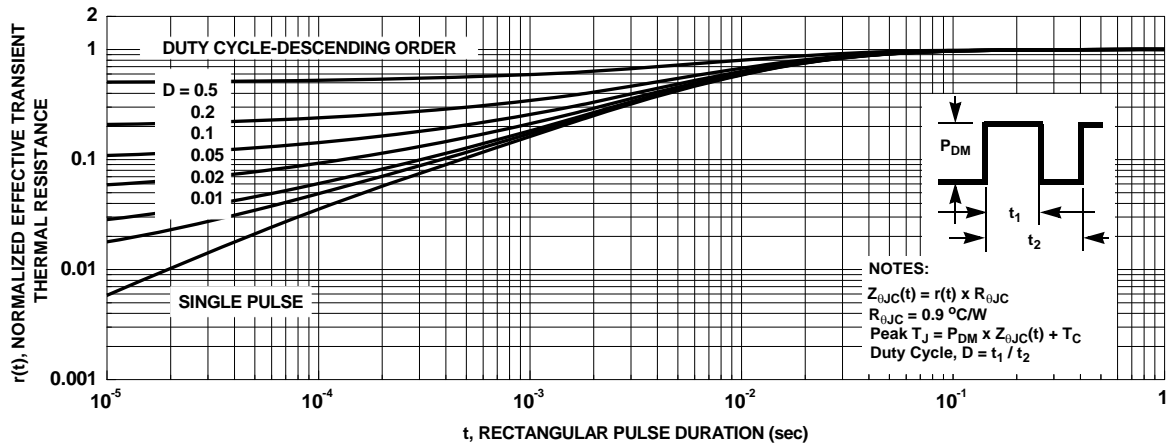


**Figure 11. Forward Bias Safe Operating Area**

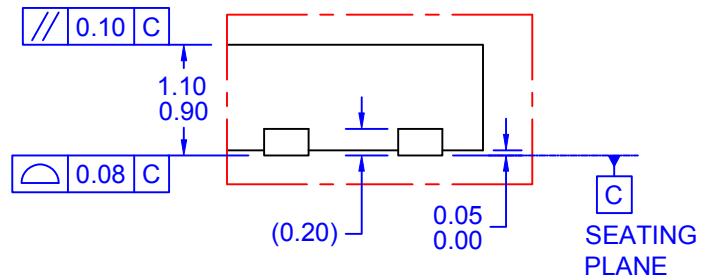
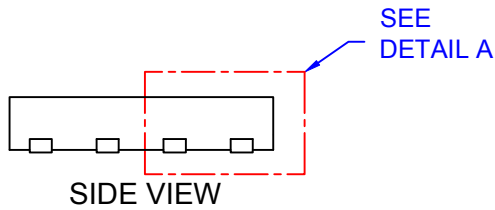
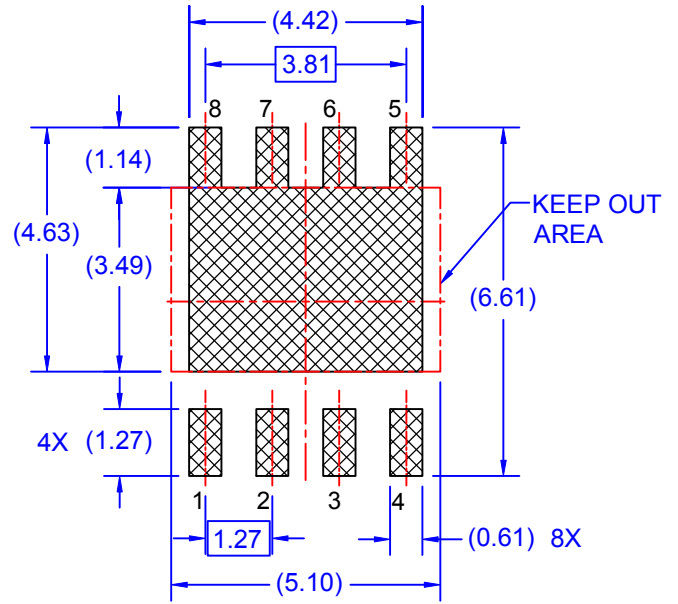
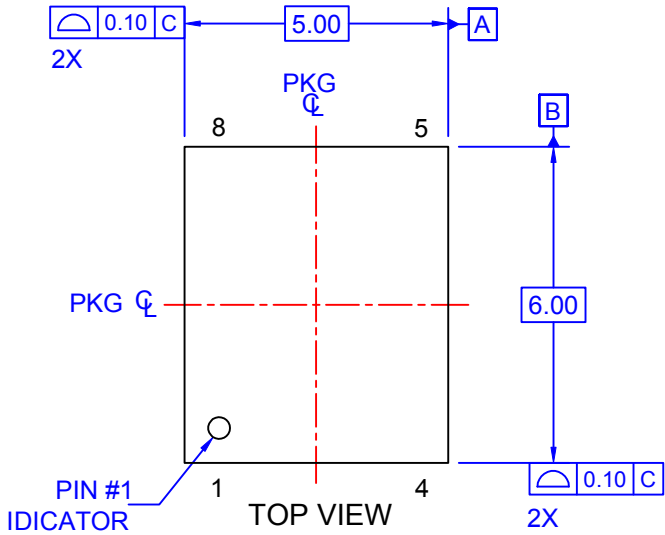


**Figure 12. Single Pulse Maximum Power Dissipation**

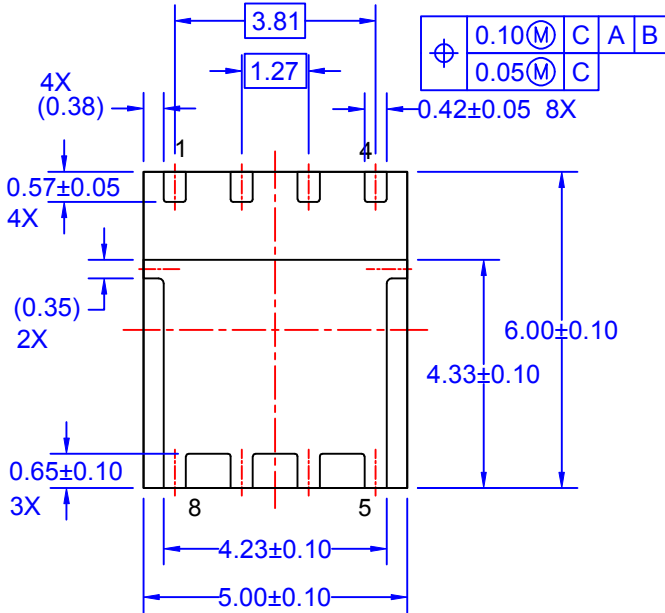
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



**Figure 13. Junction-to-Case Transient Thermal Response Curve**



**DETAIL A**  
SCALE: 2:1



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
  - D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
  - E) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
  - F) DRAWING FILE NAME: PQFN08TREV1.



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